

# An addressable quantum dot qubit with fault-tolerant control-fidelity

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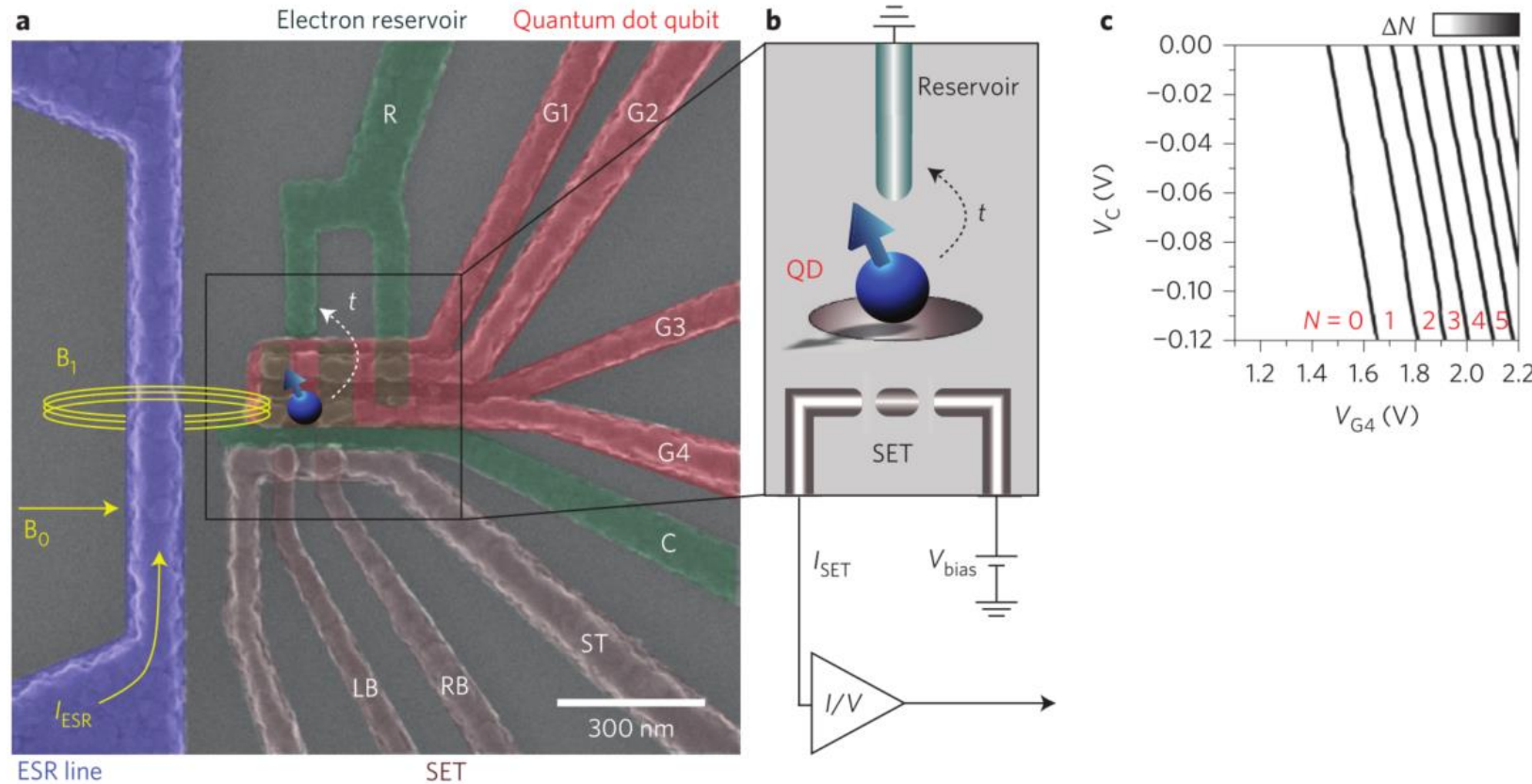
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# Contents

- electron spin qubit in  $^{28}\text{Si}$  (MOS)
- ESR stripline
- long coherence time ( $T_2 = 28\text{ms}$ )
- high control fidelity
- valley splitting

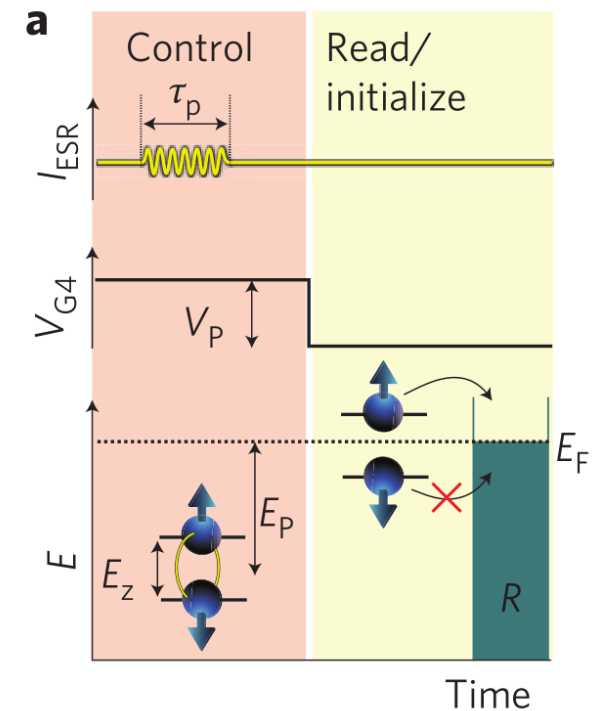
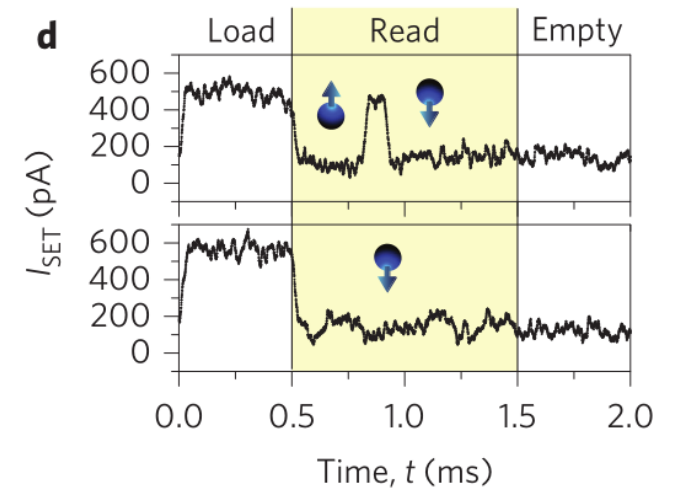
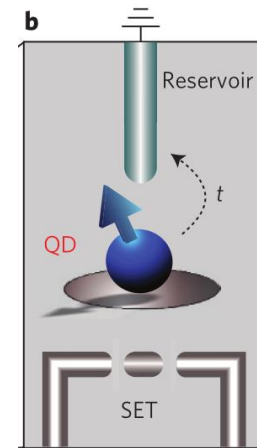
# QD Device



- QD coupled to 1 reservoir
- readout via SET (with feedback-loop)
- $T = 50\text{mK}$
- 3 layer Al-AlO gate stack on  $^{28}\text{Si}$

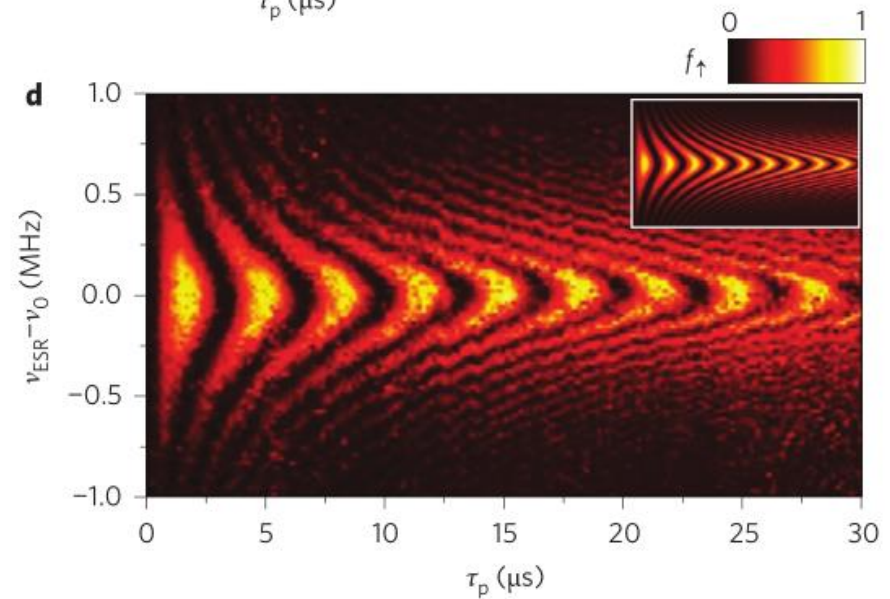
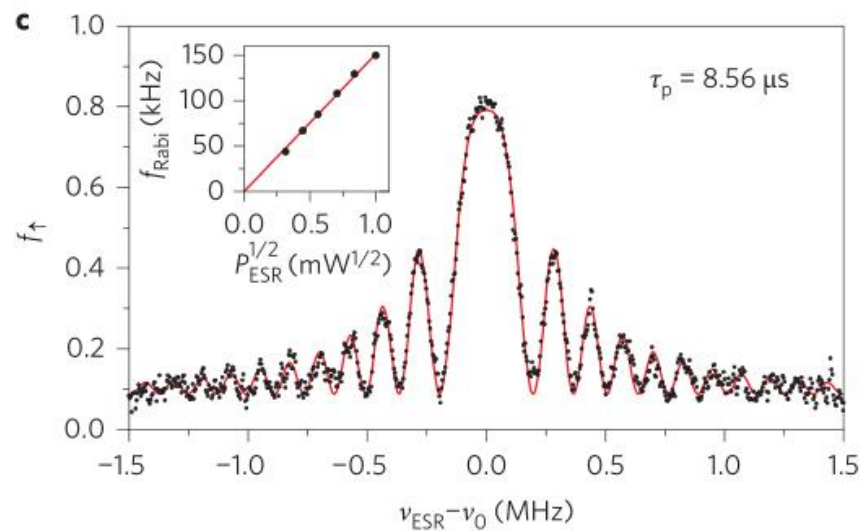
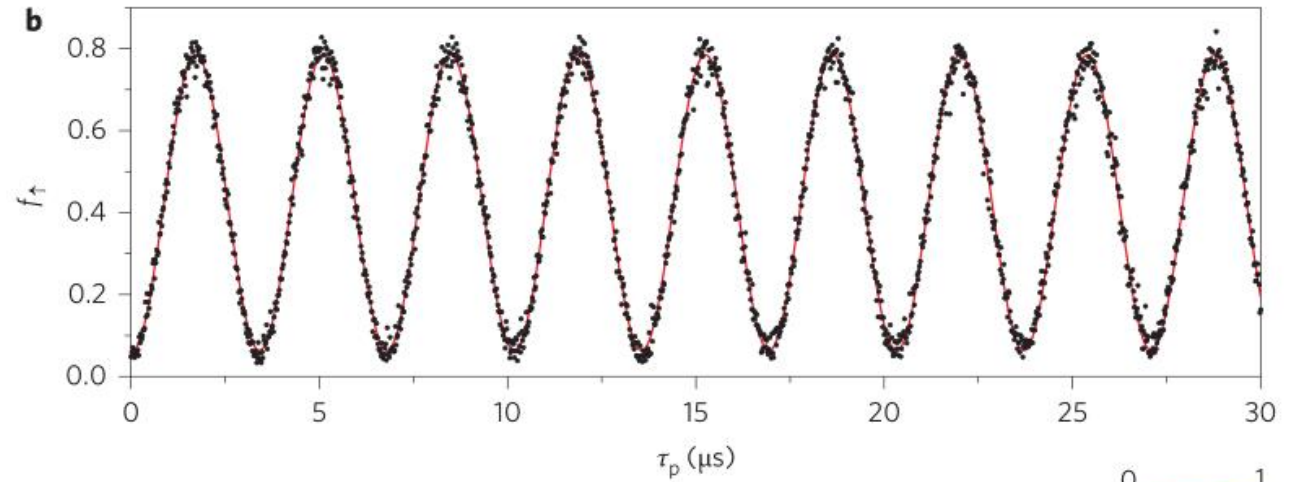
# RF and spin readout

- spin-selective tunnelling to reservoir
- single-shot spin readout
- AC B-field by AC current through transmission line
- $B = 1.4\text{T}$ ,  $g \sim 2$ ,  $f_{\text{MW}} = 39\text{GHz}$



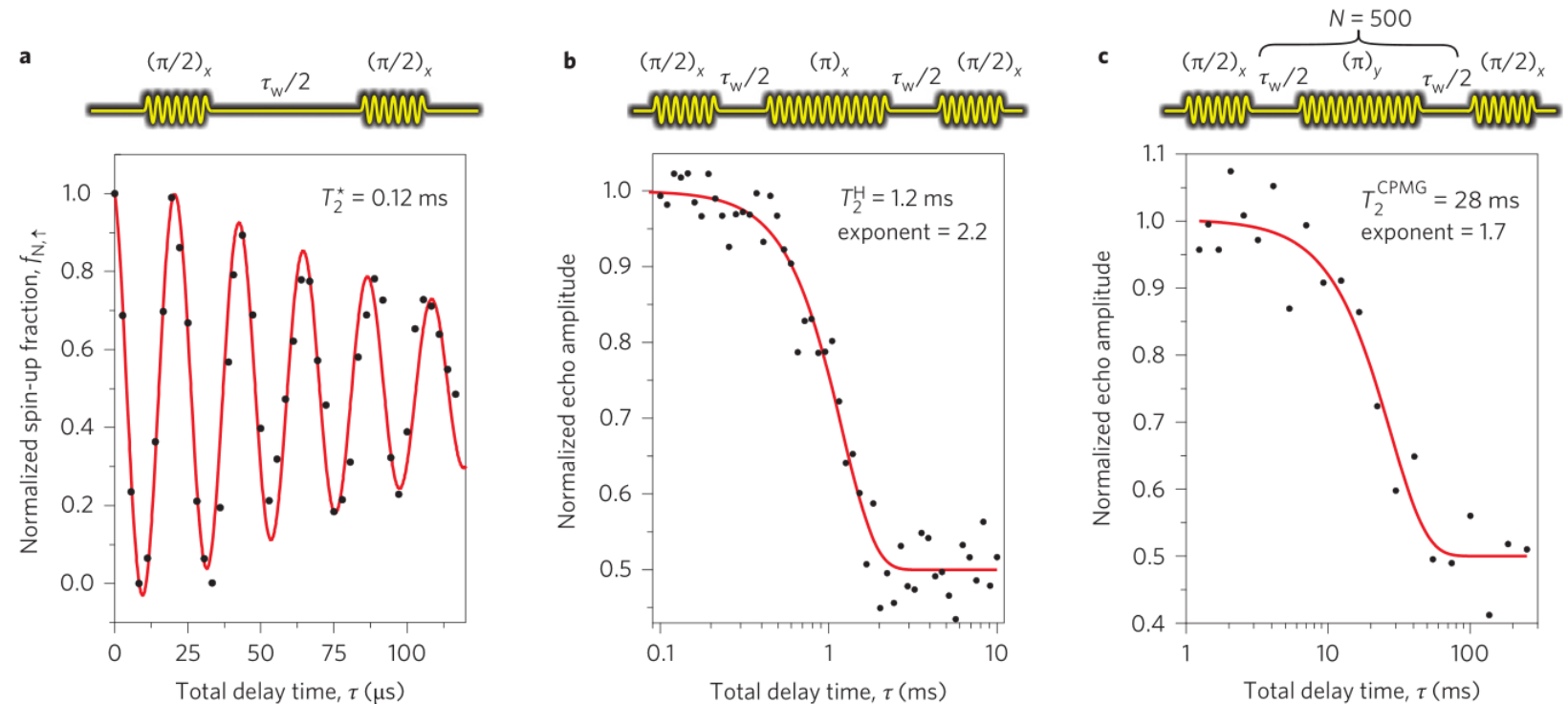
# Rabi

- $T_2^{\text{Rabi}} \sim 380 \mu\text{s}$
- $f_{\text{Rabi}} \propto \sqrt{Pwr}$
- $t_{\pi} = 1,8 \mu\text{s}$



# Ramsey, Hahn and CPMG

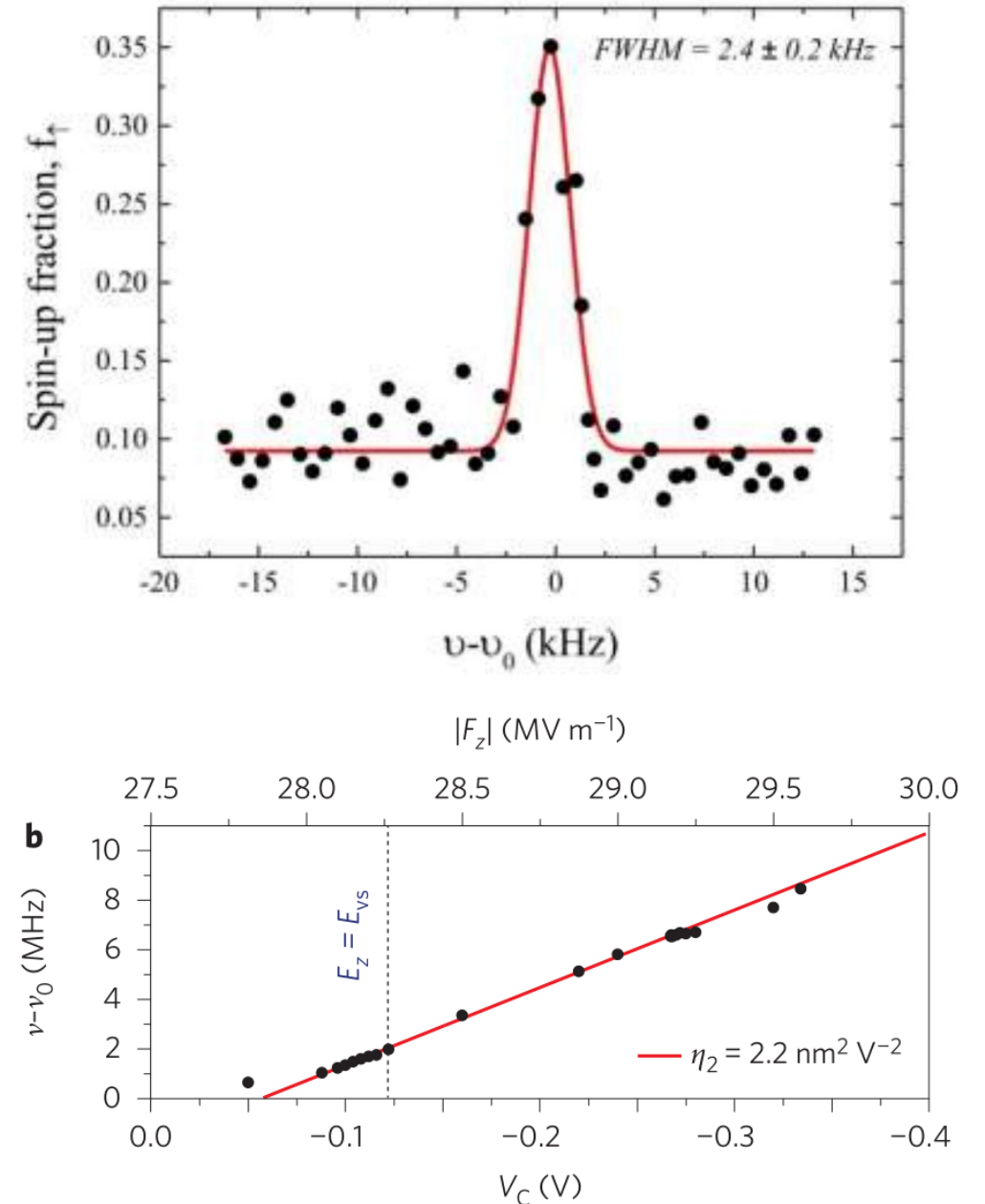
- $T_2^* = 120\mu\text{s}$
- $T_2^H = 1.2\text{ms}$
- $T_2^{\text{CPMG}} = 28\text{ms}$
- different exponents  $\rightarrow$  different noise spectra



- $10^5$  operations before decay

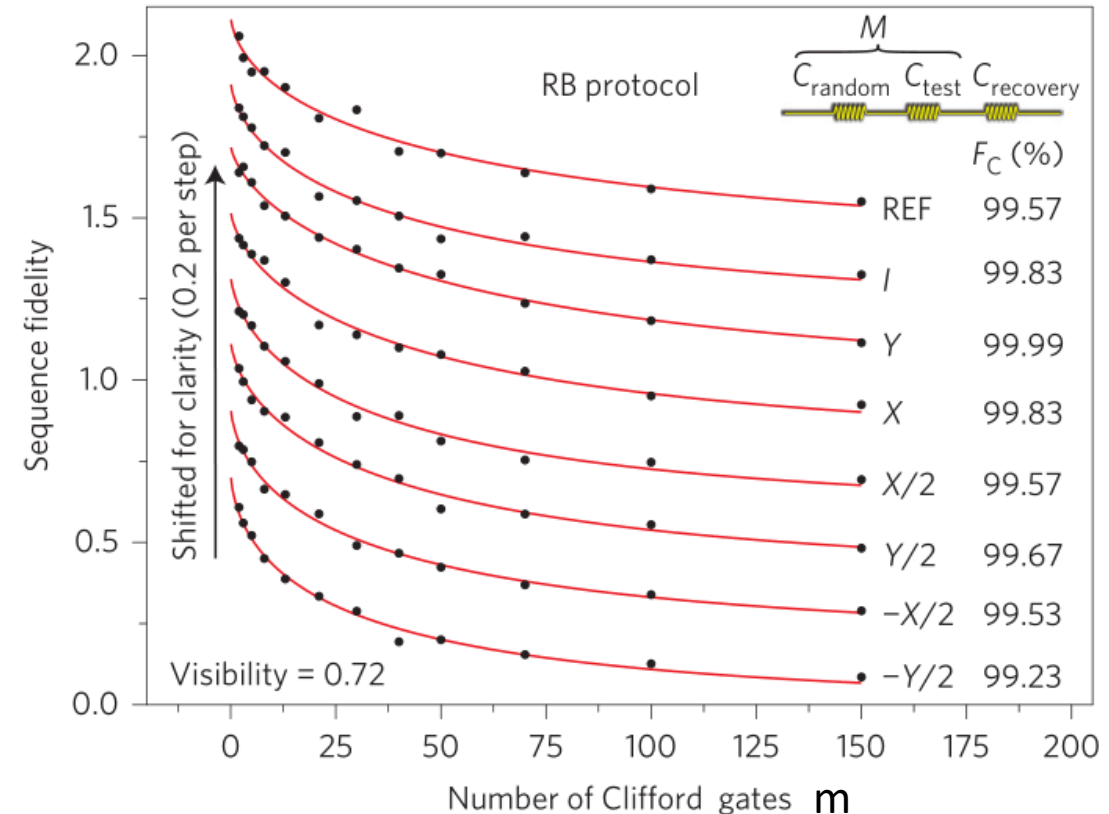
# Linewidth

- $T_2^* = 120\mu\text{s} \rightarrow$  thin linewidth  $\nu = 2.6\text{kHz}$
- agrees with linewidth measurement at Pwr=-20dbm (no more power broadening)
- electrically tunable g-factor  
 $\rightarrow$  idea: high qubit addressability in array



# Randomized benchmarking

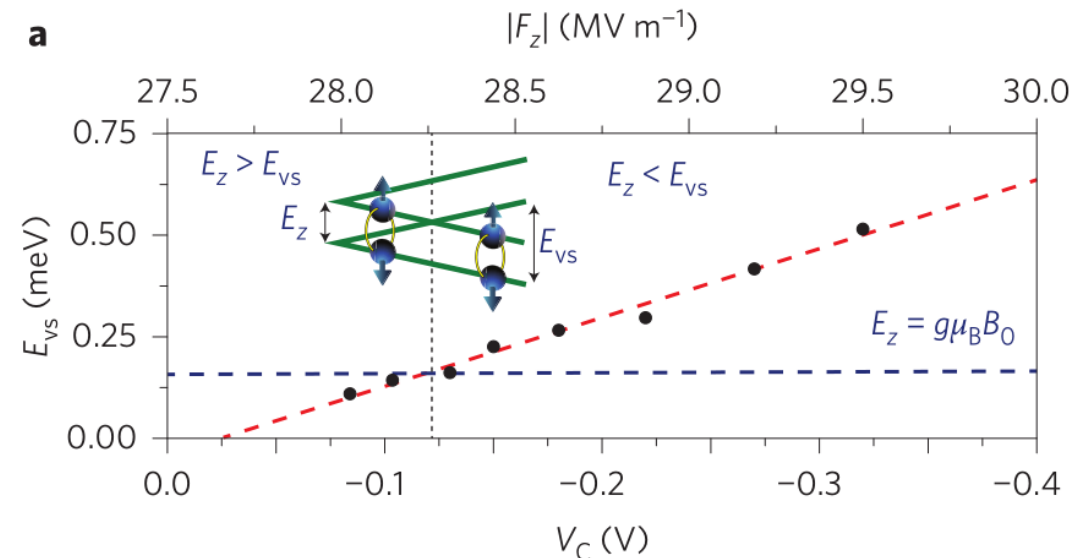
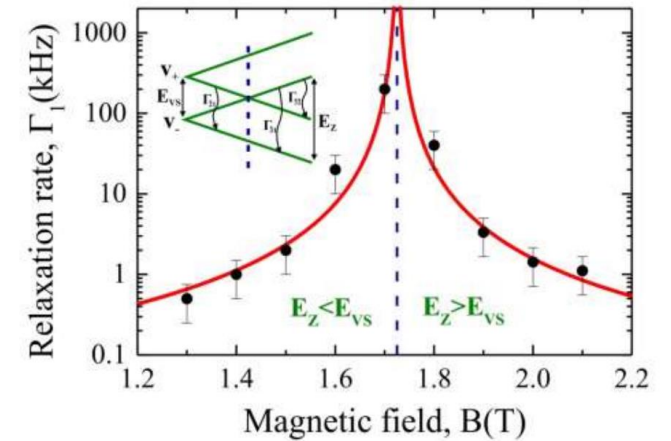
- goal: calculate gate error
- apply random series of (interleaved) gates, then recover
- get gate fidelity from sequence fidelity decay (visibility does not matter)
- fit  $f = A * \exp(-(b * m)^\alpha)$  ,  $F_C = 1 - b$
- single gate fidelity:  $F_S = 1 - b / (2 * 1.875)$
- $\rightarrow F_C > 99\%$  „fault-tolerant“





# Valley splitting

- $E_Z = E_V$  is relaxation sweet spot
- valley splitting  $\propto F_Z$  and agrees with previous device
- qubit can be operated in  $E_Z > E_V$  or  $E_Z < E_V$  regime



# Conclusion

- electrons in  $^{28}\text{Si}$   $\rightarrow$  very long coherence  $T_2^* = 120\mu\text{s}$
- CPMG improves coherence by factor 200
- address qubit electrically with tunable g-factor
- fault-tolerant gate fidelity  $> 99\%$